

# MUN5136DW1, NSBA115EDXV6

## Dual PNP Bias Resistor Transistors R1 = 100 kΩ, R2 = 100 kΩ

### PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

(T<sub>A</sub> = 25°C, common for Q1 and Q2, unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### ORDERING INFORMATION

Device	Package	Shipping†
MUN5136DW1T1G	SOT-363	3,000 / Tape & Reel
NSBA115EDXV6T1G	SOT-563	4,000 / Tape & Reel

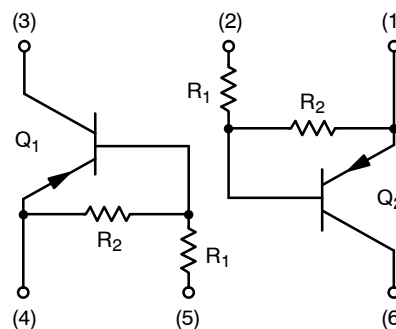
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



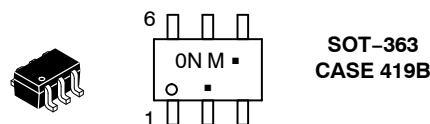
ON Semiconductor®

<http://onsemi.com>

#### PIN CONNECTIONS



#### MARKING DIAGRAMS



ON = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

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## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
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### MUN5136DW1 (SOT-363) One Junction Heated

Total Device Dissipation $T_A = 25^\circ\text{C}$	(Note 1) (Note 2)	$P_D$	187 256	mW
Derate above $25^\circ\text{C}$	(Note 1) (Note 2)		1.5 2.0	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	670 490	$^\circ\text{C}/\text{W}$

### MUN5136DW1 (SOT-363) Both Junction Heated (Note 3)

Total Device Dissipation $T_A = 25^\circ\text{C}$	(Note 1) (Note 2)	$P_D$	250 385	mW
Derate above $25^\circ\text{C}$	(Note 1) (Note 2)		2.0 3.0	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	493 325	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\theta JL}$	188 208	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

### NSBA115EDXV6 (SOT-563) One Junction Heated

Total Device Dissipation $T_A = 25^\circ\text{C}$	(Note 1)	$P_D$	357	mW
Derate above $25^\circ\text{C}$	(Note 1)		2.9	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$

### NSBA115EDXV6 (SOT-563) Both Junction Heated (Note 3)

Total Device Dissipation $T_A = 25^\circ\text{C}$	(Note 1)	$P_D$	500	mW
Derate above $25^\circ\text{C}$	(Note 1)		4.0	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- Both junction heated values assume total power is sum of two equally powered channels.

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## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , common for $Q_1$ and $Q_2$ , unless otherwise noted)

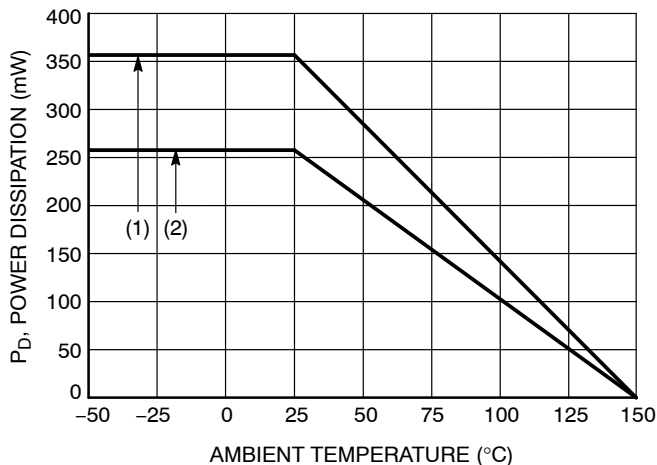
Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Base Cutoff Current ( $V_{CB} = 50\text{ V}$ , $I_E = 0$ )	$I_{CBO}$	-	-	100	nAdc
Collector-Emitter Cutoff Current ( $V_{CE} = 50\text{ V}$ , $I_B = 0$ )	$I_{CEO}$	-	-	500	nAdc
Emitter-Base Cutoff Current ( $V_{EB} = 6.0\text{ V}$ , $I_C = 0$ )	$I_{EBO}$	-	-	0.05	mAdc
Collector-Base Breakdown Voltage ( $I_C = 10\ \mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 4) ( $I_C = 2.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	50	-	-	Vdc

## ON CHARACTERISTICS

DC Current Gain (Note 4) ( $I_C = 5.0\text{ mA}$ , $V_{CE} = 10\text{ V}$ )	$h_{FE}$	80	150	-	
Collector-Emitter Saturation Voltage (Note 4) ( $I_C = 10\text{ mA}$ , $I_B = 0.3\text{ mA}$ )	$V_{CE(sat)}$	-	-	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0\text{ V}$ , $I_C = 100\ \mu\text{A}$ )	$V_{i(off)}$	-	1.2	0.5	Vdc
Input Voltage (on) ( $V_{CE} = 0.3\text{ V}$ , $I_C = 1.0\text{ mA}$ )	$V_{i(on)}$	3.0	1.6	-	Vdc
Output Voltage (on) ( $V_{CC} = 5.0\text{ V}$ , $V_B = 5.5\text{ V}$ , $R_L = 1.0\text{ k}\Omega$ )	$V_{OL}$	-	-	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0\text{ V}$ , $V_B = 0.5\text{ V}$ , $R_L = 1.0\text{ k}\Omega$ )	$V_{OH}$	4.9	-	-	Vdc
Input Resistor	$R_1$	70	100	130	$\text{k}\Omega$
Resistor Ratio	$R_1/R_2$	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq 2\%$ .



- (1) SOT-363; 1.0 x 1.0 inch Pad
- (2) SOT-563; Minimum Pad

Figure 1. Derating Curve

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## TYPICAL CHARACTERISTICS MUN5136DW1, NSBA115EDXV6

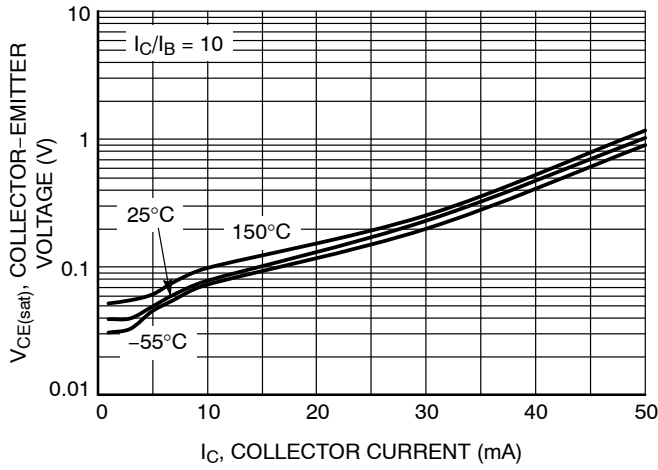


Figure 2.  $V_{CE(sat)}$  vs.  $I_C$

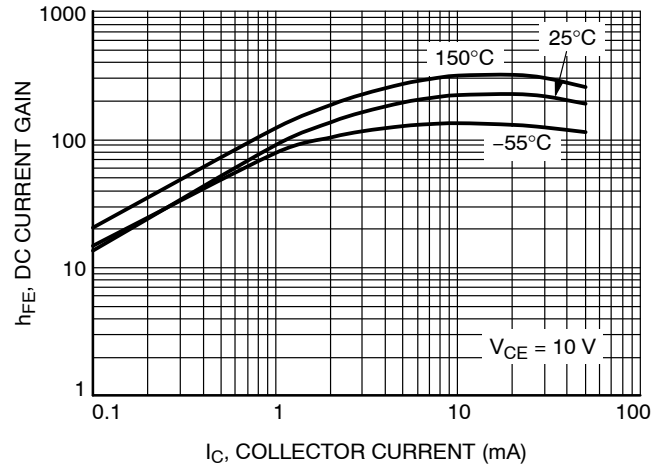


Figure 3. DC Current Gain

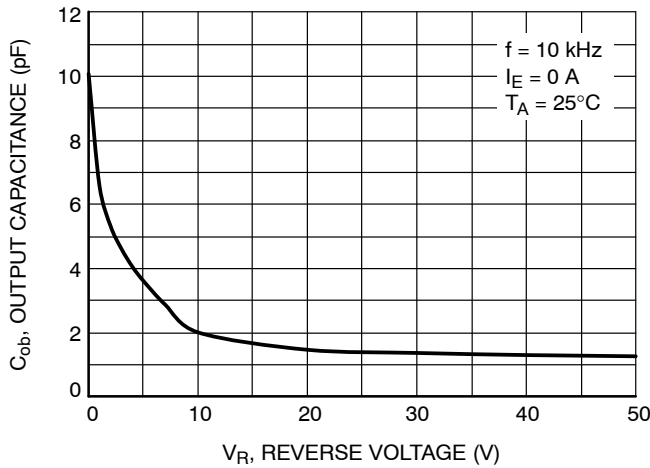


Figure 4. Output Capacitance

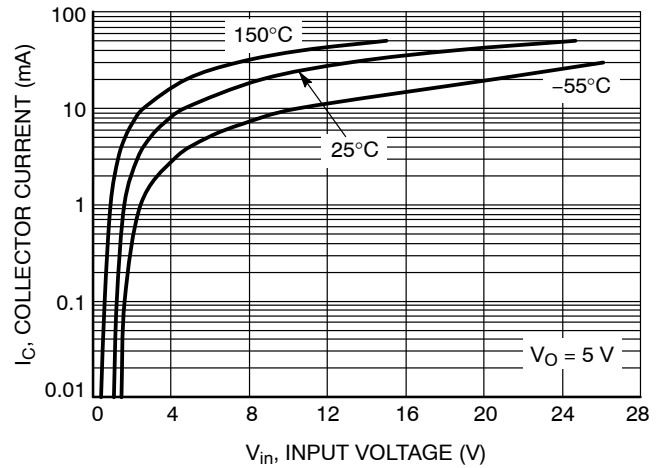


Figure 5. Output Current vs. Input Voltage

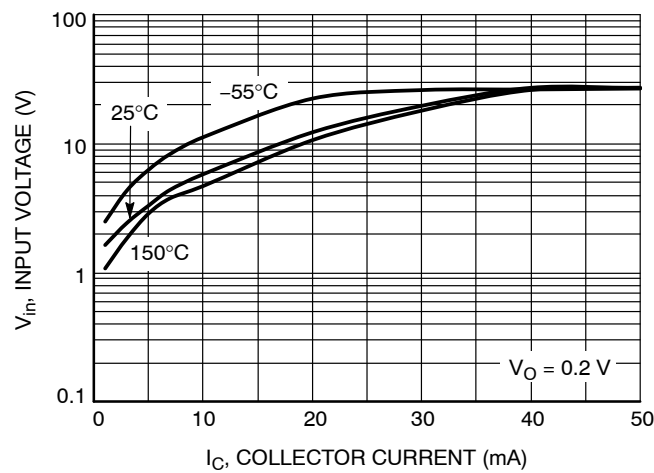
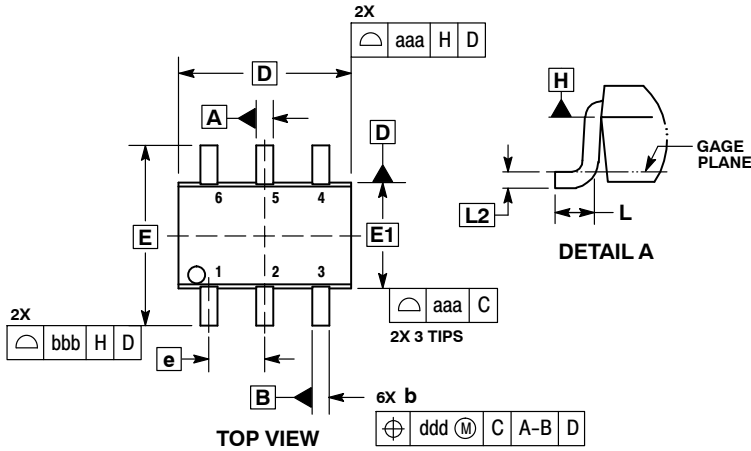


Figure 6. Input Voltage vs. Output Current

# MUN5136DW1, NSBA115EDXV6

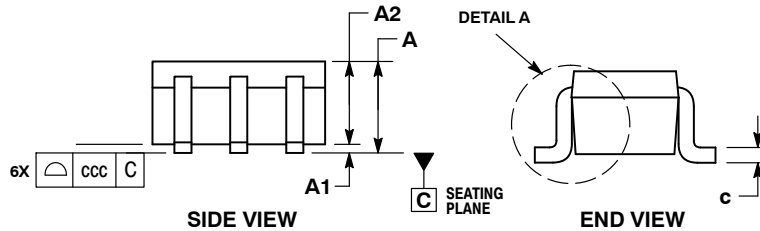
## PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363  
CASE 419B-02  
ISSUE Y

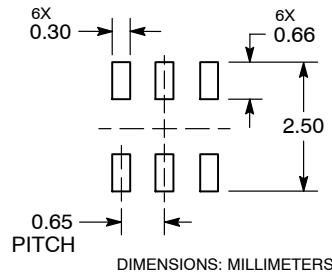


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
  4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
  5. DATUMS A AND B ARE DETERMINED AT DATUM H.
  6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
  7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		



### RECOMMENDED SOLDERING FOOTPRINT\*

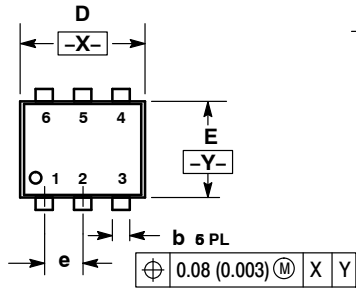


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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## PACKAGE DIMENSIONS

### SOT-563, 6 LEAD CASE 463A ISSUE F

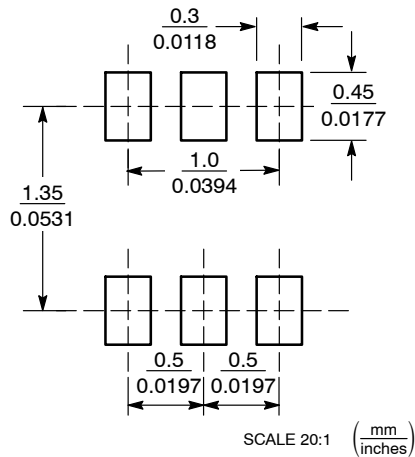


#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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